MCT6, MCT61, MCT62, MCT66

HIGH DENSITY PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS

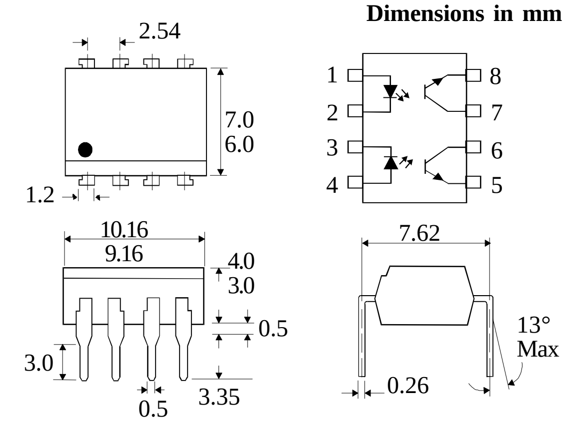
APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- **MCT6 -**
  VDE 0884 in 3 available lead form : -
  - STD
  - G form
  - SMD approved to CECC 00802

  MCT61, MCT62, MCT66 -
  VDE 0884 approval pending
- EN60950 approval pending



DESCRIPTION

The MCT6, MCT61, MCT62 & MCT66 series of optically coupled isolators consist of infrared light emitting diodes and NPN silicon photo transistors in space efficient dual in line plastic packages mounted two channels per unit.

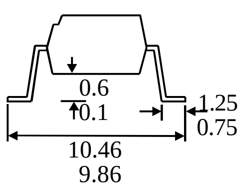
FEATURES

- Options :-
  10mm lead spread - add G after part no.
  Surface mount - add SM after part no.
  Tape&reel - add SMT&R after part no.
- High Isolation Voltage (5.3kV$_{RMS}$,7.5kV$_{PK}$)

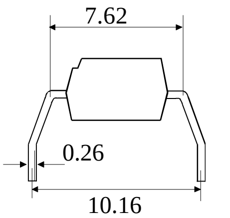
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

OPTION SM
SURFACE MOUNT



OPTION G



ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature ________ -55°C to + 125°C
Operating Temperature ______ -55°C to + 100°C
Lead Soldering Temperature
(1/16 inch (1.6mm) from case for 10 secs) 260°C

INPUT DIODE

Forward Current ________ 50mA
Reverse Voltage ________ 6V
Power Dissipation ________ 70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV$_{CEO}$ ____ 30V
Emitter-collector Voltage BV$_{ECO}$ ____ 6V
Power Dissipation ________ 150mW

POWER DISSIPATION

Total Power Dissipation ________ 200mW
(derate linearly 2.67mW/°C above 25°C)

ISOCOM COMPONENTS LTD
Unit 25B, Park View Road West,
Park View Industrial Estate, Brenda Road
Hartlepool, Cleveland, TS25 1YD
Tel: (01429) 863609 Fax :(01429) 863581

ISOCOM INC
1024 S. Greenville Ave, Suite 240,
Allen, TX 75002 USA
Tel: (214) 495-0755 Fax: (214) 495-0901
e-mail info@isocom.com
http://www.isocom.com

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)			1.50	V	I_F = 20mA
	Reverse Voltage (V_R)	3			V	I_R = 10μA
	Reverse Current (I_R)			10	μA	V_R = 3V
Output	Collector-emitter Breakdown (BV_{CEO})	30			V	I_C = 1mA (note 2)
	Emitter-collector Breakdown (BV_{ECO})	6			V	I_E = 100μA
	Collector-emitter Dark Current (I_{CEO})			100	nA	V_{CE} = 10V
Coupled	Current Transfer Ratio (CTR) (Note 2)					
	MCT6	20			%	10mA I_F, 10V V_{CE}
	MCT61	50			%	5mA I_F, 5V V_{CE}
	MCT62	100			%	5mA I_F, 5V V_{CE}
	MCT66	6			%	10mA I_F, 10V V_{CE}
	Collector-emitter Saturation Voltage V_{CESAT}					
	MCT6,61,62			0.4	V	16mA I_F, 2mA I_C
	MCT66			0.4	V	40mA I_F, 2mA I_C
	Input to Output Isolation Voltage V_{ISO}	5300			V_{RMS}	See note 1
	Input to Output Isolation Voltage V_{ISO}	7500			V_{PK}	See note 1
	Input-output Isolation Resistance R_{ISO}	$5x10^{10}$			Ω	V_{IO} = 500V (note 1)
	Output Rise Time, Fall Time tr , tf		2.4		μs	I_C = 2mA, V_{CC} = 10V, R_L = 100Ω (Fig. 1)
	Output Rise Time, Fall Time tr , tf		15		μs	I_C = 2mA, V_{CC} = 10V, R_L = 1kΩ (Fig. 2)

Note 1 Measured with input leads shorted together and output leads shorted together.
Note 2 Special Selections are available on request. Please consult the factory.

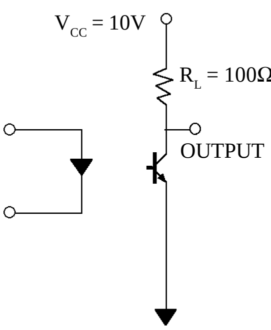


FIG 1

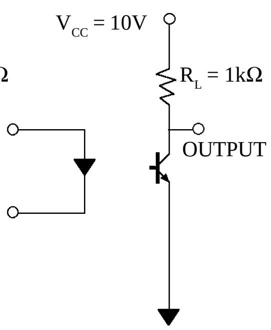
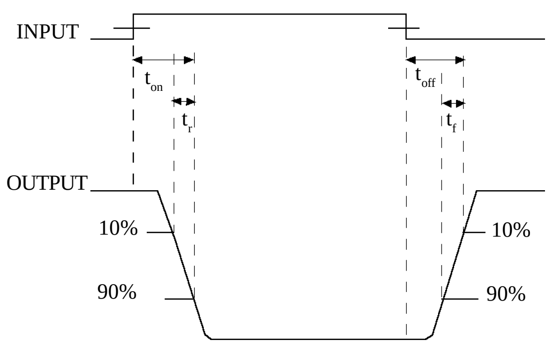
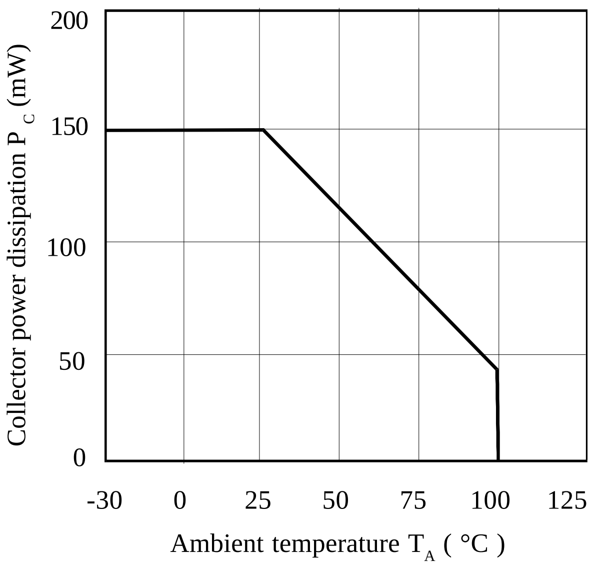


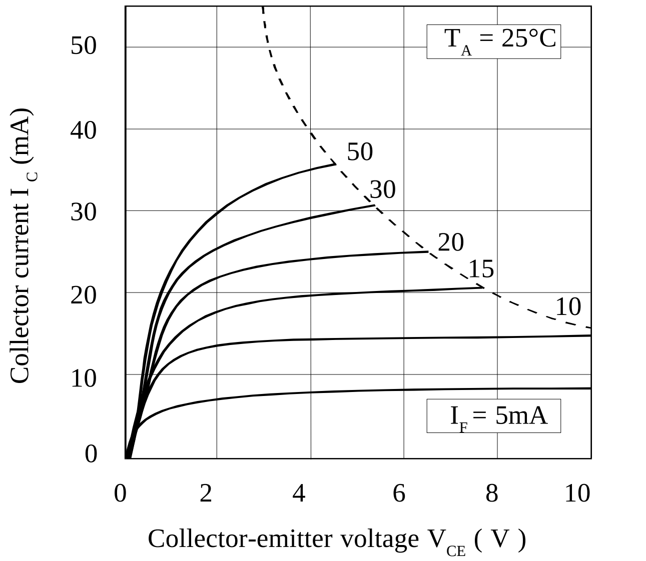
FIG 2



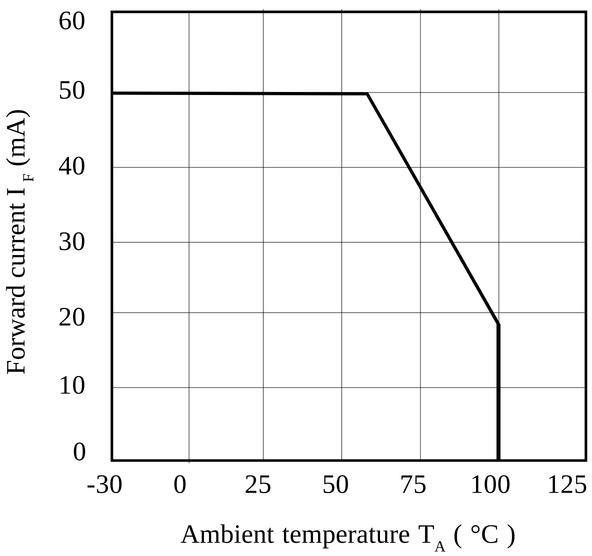
Collector Power Dissipation vs. Ambient Temperature



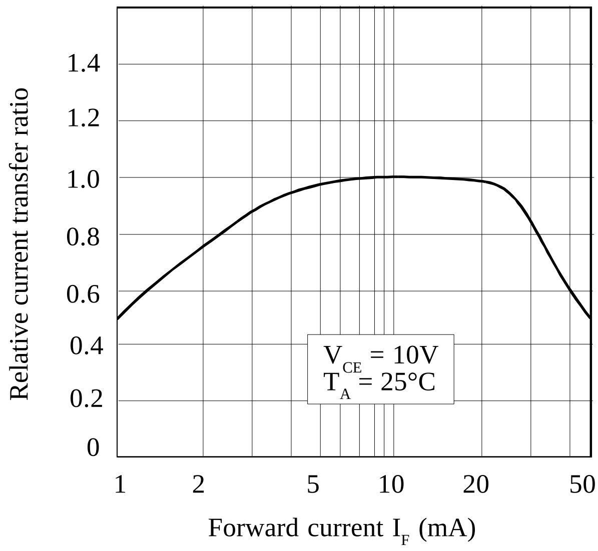
Collector Current vs. Collector-emitter Voltage



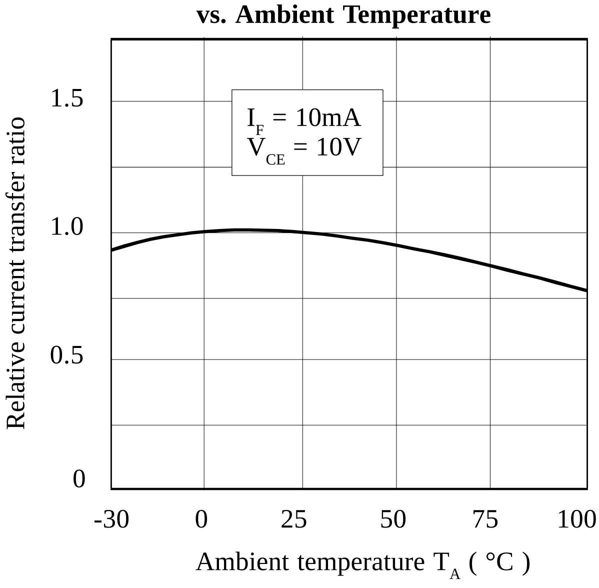
Forward Current vs. Ambient Temperature



Relative Current Transfer Ratio vs. Forward Current



Relative Current Transfer Ratio vs. Ambient Temperature



Collector-emitter Saturation Voltage vs. Ambient Temperature